

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention

SEMICONDUCTOR DEVICE AND SEMICONDUCTOR
SUBSTRATE, AND METHOD OF FABRICATING THE SAME

Application Number :

Confirmation Number:

First Named Applicant: Masahiro ISHIDA

Attorney Docket Number: 28569.4136

Art Unit: 2811

Examiner: Sara W. Crane

Search string: (6111277 or 6337233 or 5834325 or 6121634 or 6153010 or 6015979 or 6051849
or 6177688 or 5285086 or 5032893 or 5294808 or 5208182).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

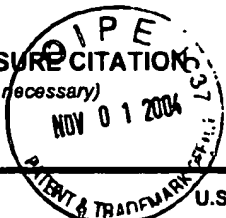
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
SOL	1	6111277	2000-08-29	Ikeda			
	2	6337233	2002-01-08	Kim, et al.			
	3	5834325	1998-11-10	Motika, et al.			
	4	6121634	2000-09-19	Saito, et al.			
	5	6153010	2000-11-28	Kiyoku, et al.			
	6	6015979	2000-01-18	Sugiura, et al.			
	7	6051849	2000-04-18	Davis, et al.			
	8	6177688	2001-01-23	Linthicum, et al.			
	9	5285086	1994-02-08	Fitzgerald, et al.			
	10	5032893	1991-07-16	Fitzgerald, Jr., et al.			
	11	5294808	1994-03-15	Lo			
SOL	12	5208182	1993-05-04	Narayan, et al.			

Signature

Examiner Name	Date
CRANE	12/2004

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



ATTY DOCKET NO.

28569.4136

SERIAL NO.

10/711,698

Masahiro ISHIDA, et al.

FILING

September 30, 2004

GROUP

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
SWL	6-216037	01/13/1993	Japan				
}	03-133182	06/06/1991	Japan				
}	05-036602	02/12/1993	Japan				
}	57-115849	07/19/1982	Japan				
SWL	09/172200	06/30/1997	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWL		"Anisotropic Exptaxail Growth in GaN Selective Area Exptaxy", Kapolenek, et al., Appl. Phys. Letts, vol. 71, 9/1/9197, pp. 1204-1206
JWL		"Lateral Epitaxy of Low Defect Density GaN Layers Via Organomatallic Vapor Phase Epitaxy", Nam, et al., Appl. Phys. Letts., vol. 71, 1997, pp 2638-2640

EXAMINER

CRANE

DATE CONSIDERED

12/2004

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Masahiro ISHIDA, et al.	
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
SWL	06-268257 A	09/22/1994	Japan				
SWL	10-312971 A	11/24/1998	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER CRANE	DATE CONSIDERED 12/2004
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